



ZX5T853G

100V NPN MEDIUM POWER LOW SATURATION TRANSISTOR IN SOT223

#### **Features**

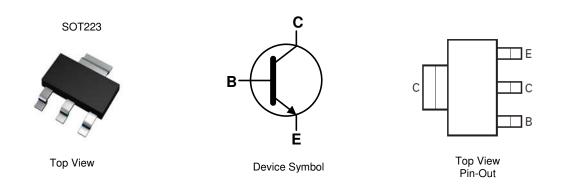
- BV<sub>CEO</sub> > 100V
- I<sub>C</sub> = 6A High Continuous Collector Current
- I<sub>CM</sub> = 10A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(sat)</sub> < 35mV
- R<sub>SAT</sub> = 36mΩ at 6A for a Low Equivalent On-Resistance
- hFE Specified Up to 10A for a High Gain Hold Up
- Complementary PNP Type: ZX5T953G
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (2)
- Weight: 0.112 grams (Approximate)

## **Applications**

- Motor Driving
- Line Switching
- High Side Switches



### Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZX5T853GTA	AEC-Q101	X5T853	7	12	1,000

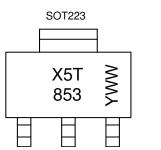
Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



X5T 853 = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 5= 2015) WW or  $\overline{W}W$  = Week Code (01~53)



# Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	200	V
Collector-Emitter Voltage	V <sub>CEO</sub>	100	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	Ι <sub>C</sub>	6	А
Peak Pulse Current	I <sub>CM</sub>	10	А

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)		3.0 24	W	
Linear Derating Factor	(Note 6)	PD	1.6 12.8	mW/°C	
Thermal Resistance, Junction to Ambient	(Note 5)	R <sub>⊕JA</sub>	42		
Thermal Resistance, Junction to Amblent	(Note 6)	$R_{ ext{ heta}JA}$	78	°C/W	
Thermal Resistance Junction to Lead	(Note 7)	$R_{ ext{ heta}JL}$	10.5		
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C		

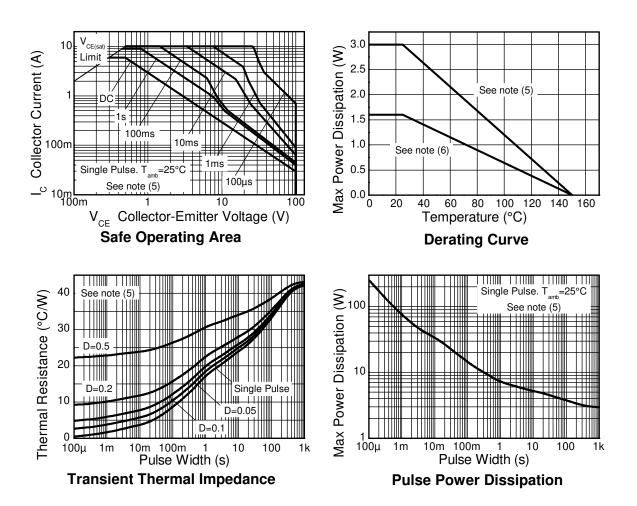
#### ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

5. For a device surface mounted on 52mm x 52mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is Notes: b) The device surface modified on Schmit X 1.5mm FR4 PCB with high coverage of semicondense when operating in a steady-state condition.
c) Same as Note 5, except the device is surface mounted on 25mm x 25mm with 1oz copper.
7. Thermal resistance from junction to solder-point (at the end of the collector lead).
8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



## **Thermal Characteristics and Derating Information**





## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

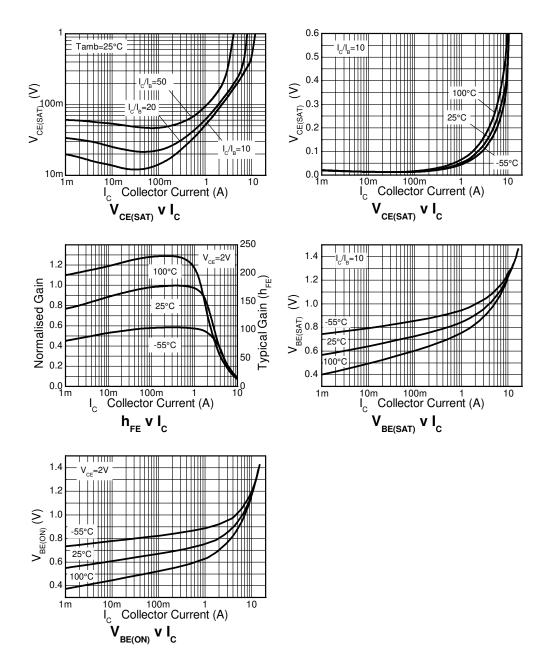
Characteristic	Symbol	Min	Turn	Мах	Unit	Test Condition
	Symbol		Тур	Max		
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	200	235	-	V	I <sub>C</sub> = 100μA
Collector-Emitter Breakdown Voltage	BV <sub>CER</sub>	200	235	-	V	$I_{C} = 1\mu A, RB \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	100	115	-	V	$I_{C} = 10 \text{mA}$
Emitter-Base Breakdown Voltage	BVEBO	7	8.1	-	V	$I_E = 100 \mu A$
Collector-Base Cut-Off Current	1		<1	20	nA	V <sub>CB</sub> = 150V
Collector-Dase Out-On Guilent	I <sub>CBO</sub>	-	-	0.5	μΑ	$V_{CB} = 150V, T_A = +100^{\circ}C$
Collector-Emitter Cut-Off Current	ICER		-	20	nA	V <sub>CB</sub> = 150V
	R ≤ 1kΩ	-	-	0.5	μΑ	$V_{CB} = 150V, T_A = +100^{\circ}C$
Emitter Cut-Off Current	I <sub>EBO</sub>	-	-	10	nA	$V_{EB} = 6V$
		100	230	-	-	$I_{C} = 10mA, V_{CE} = 2V$
Statia Farward Current Transfer Datia (Nata 0)	L.	100	200	300		$I_C = 2A, V_{CE} = 2V$
Static Forward Current Transfer Ratio (Note 9)	h <sub>FE</sub>	30	60	-		$I_C = 5A, V_{CE} = 2V$
		10	20	-		I <sub>C</sub> = 10A, V <sub>CE</sub> = 2V
		-	21	35	mV	$I_{C} = 100 \text{mA}, I_{B} = 5 \text{mA}$
O - II		-	50	65		$I_{\rm C} = 1$ A, $I_{\rm B} = 100$ mA
Collector-Emitter Saturation Voltage (Note 9)	V <sub>CE(sat)</sub>	-	95	125		$I_{\rm C} = 2A, I_{\rm B} = 100 {\rm mA}$
		-	180	220		$I_{\rm C} = 5A, I_{\rm B} = 500 \text{mA}$
Base-Emitter Saturation Voltage (Note 9)	V <sub>BE(sat)</sub>	-	1,020	1,120	mV	$I_{\rm C} = 5A, I_{\rm B} = 500 {\rm mA}$
Base-Emitter Turn-On Voltage (Note 9)	V <sub>BE(on)</sub>	-	920	1,000	mV	$I_C = 5A, V_{CE} = 2V$
Output Capacitance (Note 9)	C <sub>obo</sub>	-	26	-	pF	V <sub>CB</sub> = 10V. f = 1MHz
Transition Frequency	f <sub>T</sub>	-	130	-	MHz	$V_{CE} = 10V, I_C = 100mA$ f = 50MHz
Switching Time	t <sub>on</sub>	-	41	-	20	$V_{CC} = 10V, I_{C} = 1A$
Switching Time	t <sub>off</sub>	-	1,010	-	ns	$I_{B1} = -I_{B2} = 100 \text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



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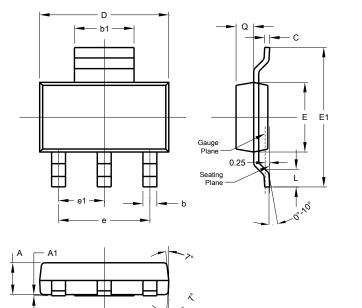
## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)





#### Package Outline Dimensions

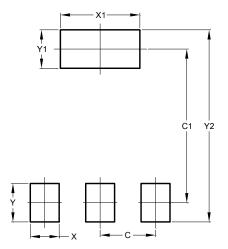
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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